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Kind regards,

Team Nexperia



2 A low V_F MEGA Schottky barrier rectifier Rev. 01 — 15 December 2009

Product data sheet

Product profile 1.

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection. PMEG3020EPA is encapsulated in an ultra thin SOT1061 leadless small Surface-Mounted Device (SMD) plastic package with medium power capability.

1.2 Features

- Average forward current: I_{F(AV)} ≤ 2 A
- Reverse voltage: V_B ≤ 30 V
- Low forward voltage
- Exposed heat sink (cathode pad) for excellent thermal and electrical conductivity
- Leadless small SMD plastic package with medium power capability
- AEC-Q101 qualified

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Reverse polarity protection
- Low power consumption applications
- Battery chargers for mobile equipment

1.4 Quick reference data

Table 1. Quick reference data

 $T_i = 25 \ ^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
I _{F(AV)}	average forward current	square wave; $\delta = 0.5$; f = 20 kHz				
		$T_{amb} \le 65 \ ^{\circ}C$	<u>[1]</u> -	-	2	А
		$T_{sp} \le 140 \ ^{\circ}C$	-	-	2	А
V _R	reverse voltage		-	-	30	V
V _F	forward voltage	I _F = 2 A	-	410	470	mV
I _R	reverse current	$V_R = 30 V$	-	435	2500	μA

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.



2. Pinning information

Table 2.	Pinning	
Pin	Description	Simplified outline Graphic symbol
1	anode	
2	anode	3 3 1, 2
3	cathode	006aab624
		1 2
		Transparent top view

3. Ordering information

Table 3. Ordering information				
Type number Package				
	Name	Description	Version	
PMEG3020EPA	HUSON3	plastic thermal enhanced ultra thin small outline package; no leads; three terminals; body $2 \times 2 \times 0.65$ mm	SOT1061	

4. Marking

Table 4.	Marking codes	
Type num	ıber	Marking code
PMEG302	20EPA	A2

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _R	reverse voltage	$T_j = 25 \ ^{\circ}C$	-	30	V
I _{F(AV)}	average forward current	square wave; δ = 0.5; f = 20 kHz			
		$T_{amb} \le 65 \ ^{\circ}C$	<u>[1]</u> -	2	А
		$T_{sp} \le 140 \ ^{\circ}C$	-	2	А
I _{FRM}	repetitive peak forward current	$\begin{array}{l} t_p \leq 1 \ ms; \\ \delta \leq 0.25 \end{array}$	[2] _	7	A
I _{FSM}	non-repetitive peak forward current	square wave; t _p = 8 ms	[2][3] _	17	A
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[4][5]</u>	500	mW
			[4][6]	960	mW
			[4][1]	1800	mW

Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

[2] Both anode pins connected.

[3] $T_j = 25 \,^{\circ}C$ prior to surge.

[4] Reflow soldering is the only recommended soldering method.

[5] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[6] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient		in free air	[1][2]			
		[3]	-	250	K/W	
			<u>[4]</u> _	-	130	K/W
			[5]	-	70	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		<u>[6]</u> _	-	12	K/W

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

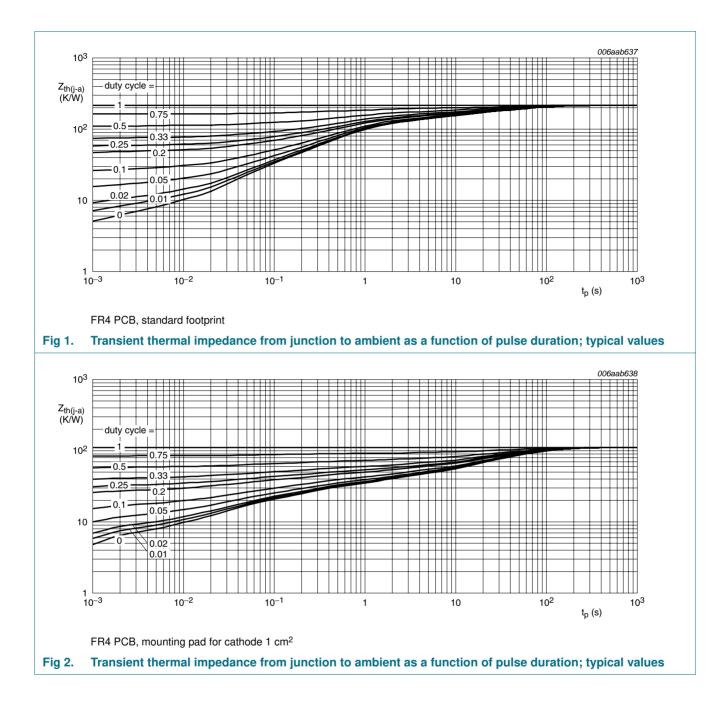
[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

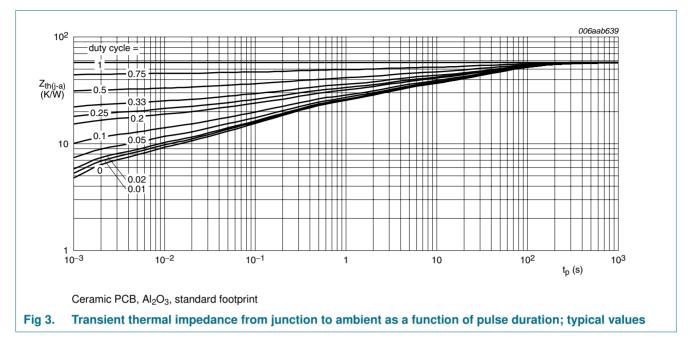
[4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

[5] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

[6] Soldering point of cathode tab.



2 A low V_F MEGA Schottky barrier rectifier



7. Characteristics

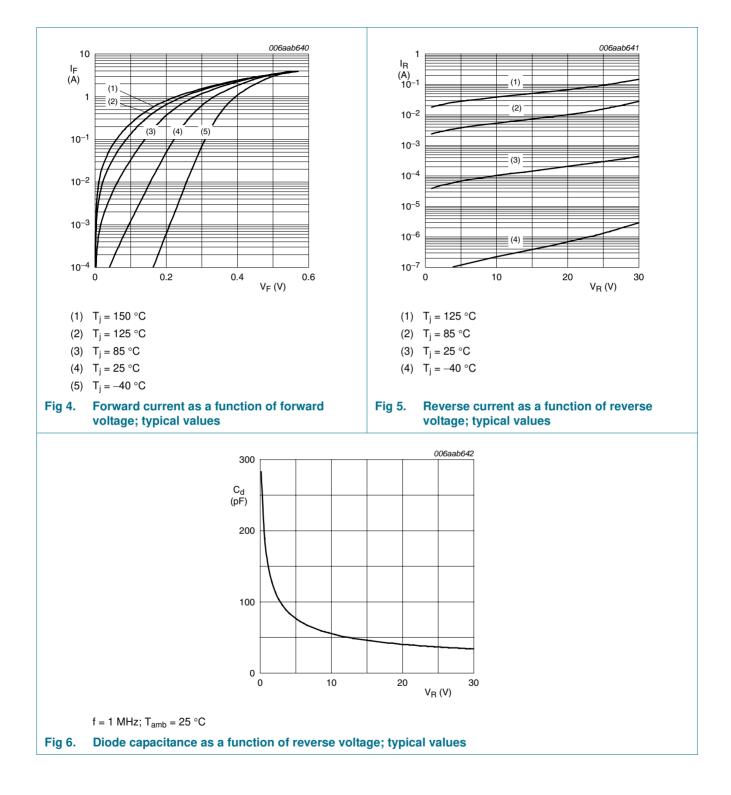
Table 7.Characteristics

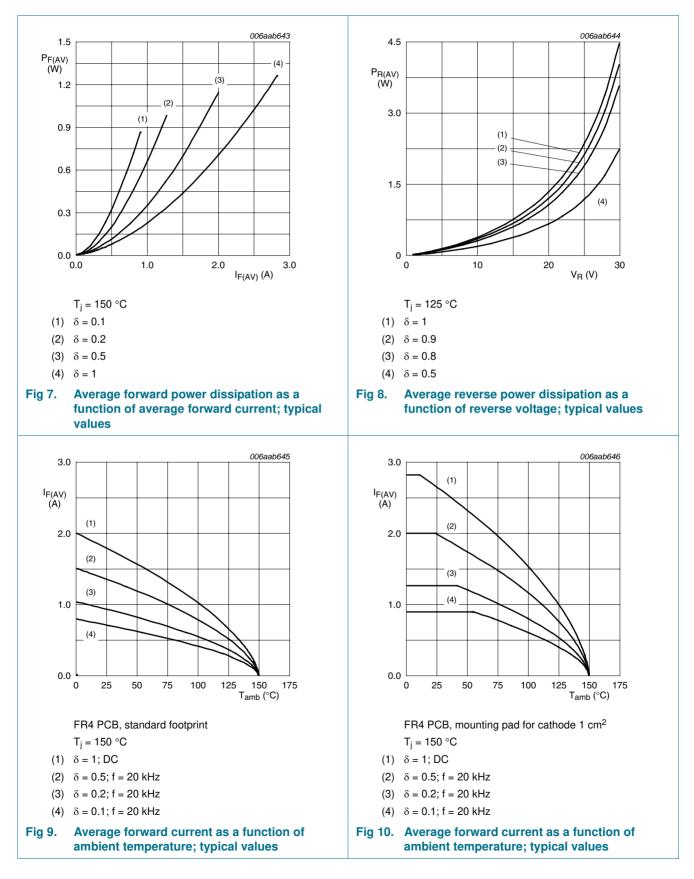
$T_{i} = 25$	°C	unless	otherwise	specified
11-20		unicoo		SDECITIEU.

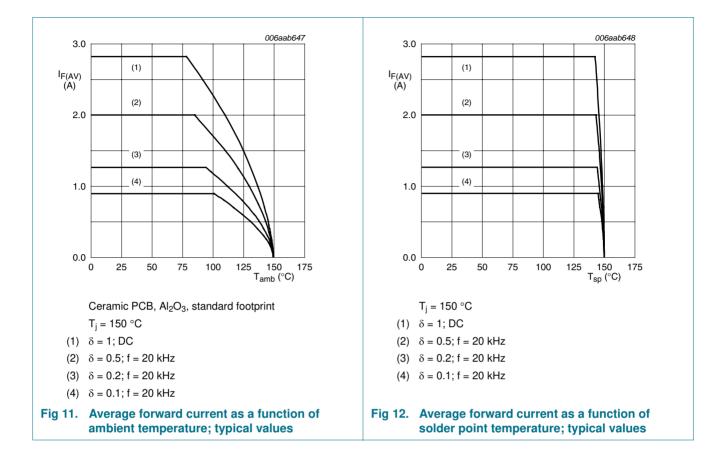
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _F forward voltage	forward voltage	I _F = 0.5 A	-	290	-	mV
	I _F = 1 A	-	335	-	mV	
	I _F = 2 A	-	410	470	mV	
I _R reverse current	V _R = 10 V	-	100	-	μA	
		V _R = 30 V	-	435	2500	μA
C _d	diode capacitance	f = 1 MHz				
		$V_R = 1 V$	-	150	-	pF
		V _R = 10 V	-	55	-	pF
t _{rr}	reverse recovery time	е	<u>[1]</u> _	47	-	ns

[1] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA.

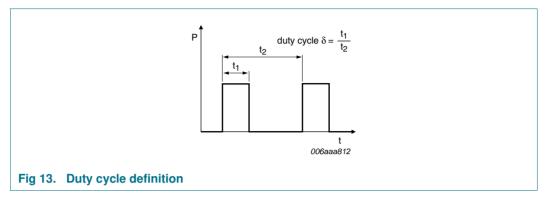
Product data sheet







8. Test information



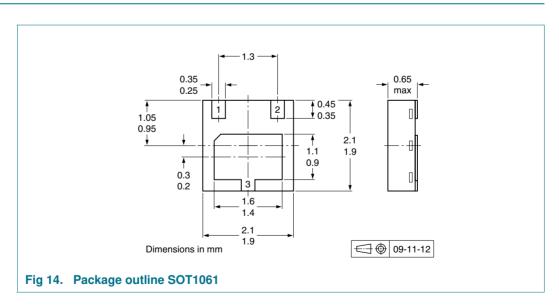
The current ratings for the typical waveforms as shown in Figure 9, 10, 11 and 12 are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current,

 $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

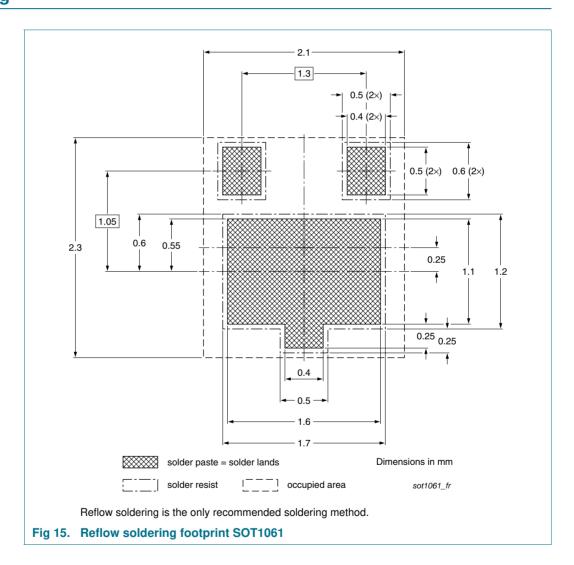
9. Package outline



10. Packing information

Table 8. Packing methods The indicated -xxx are the last three digits of the 12NC ordering code.[1]				
Type number Package Description Packing quantity				
			3000	
PMEG3020EPA	SOT1061	4 mm pitch, 8 mm tape and reel	-115	
[1] For further info	ormation and th	e availability of packing methods, see Section 14.		

11. Soldering



12. Revision history

Table 9. Revision	n history				
Document ID	Release date	Data sheet status	Change notice	Supersedes	
PMEG3020EPA_1	20091215	Product data sheet	-	-	

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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